

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

3N247-M SERIES
3N254-M SERIES

SILICON BRIDGE RECTIFIER

CASE B-M

DESCRIPTION

The CENTRAL SEMICONDUCTOR 3N247-M, 3N254-M series types are silicon single phase full wave bridge rectifiers designed for general purpose applications.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

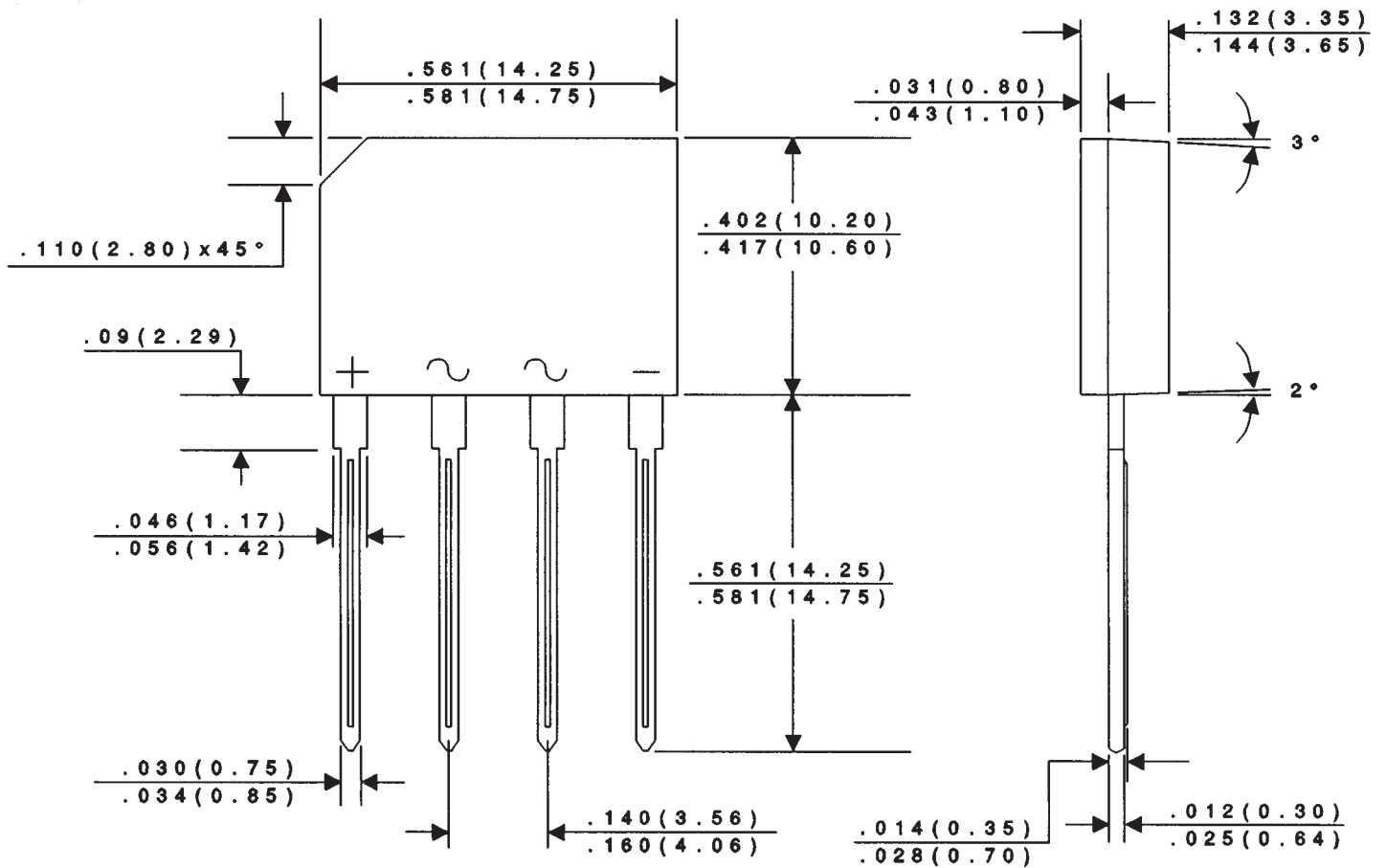
	SYMBOL	3N	3N	3N	3N	3N	3N	UNITS
		<u>247-M</u>	<u>248-M</u>	<u>249-M</u>	<u>250-M</u>	<u>251-M</u>	<u>252-M</u>	
		3N	3N	3N	3N	3N	3N	
		<u>254-M</u>	<u>255-M</u>	<u>256-M</u>	<u>257-M</u>	<u>258-M</u>	<u>259-M</u>	
Peak Repetitive Reverse Voltage	V_{RRM}	100	200	400	600	800	1000	V
DC Blocking Voltage	V_R	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	280	420	560	700	V
Average Forward Current (3N247-M Series @ $T_A=75^\circ\text{C}$) I_O				1.5				A
Average Forward Current (3N254-M Series @ $T_A=55^\circ\text{C}$) I_O				2.0				A
Peak Forward Surge Current (3N247-M Series)	I_{FSM}				30			A
Peak Forward Surge Current (3N254-M Series)	I_{FSM}				55			A
Operating and Storage Junction Temperature	T_J, T_{stg}			-65 to +150				$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>MAX</u>	<u>UNITS</u>
V_F	$I_F=3.14\text{A}$ (3N247-M Series)		1.3	V
V_F	$I_F=3.14\text{A}$ (3N254-M Series)		1.1	V
I_R	$V_R=\text{Rated } V_{RRM}$		10	μA

(OVER)

CASE B-M - MECHANICAL OUTLINE



All Dimensions in Inches (mm).